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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shunpei Yamazaki et al. Art Unit : 2811
Serial No. : 10/718,584 Examiner : Unknown
Filed : November 24, 2003 Confirmation No.: 1684
Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

MAIL STOP AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Applicants submit the references listed on the attached form PTO-1449. In accordance with the PTO's waiver of 37 CFR 1.98 (a)(2)(iii), only copies of foreign patent documents and non-patent references are enclosed.

This statement is being filed before the receipt of a first Office Action on the merits.
Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: November 4, 2004



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| Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b)) | U.S. Department of Commerce Patent and Trademark Office | Attorney's Docket No. 12732-092002 | Application No. 10/718,584 |
| | Applicant Shunpei Yamazaki et al. | | |
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